

# **DualCool™ N-Channel NexFET™ Power MOSFETs**

Check for Samples: CSD16322Q5C

### **FEATURES**

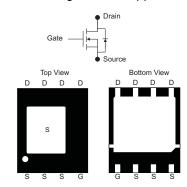
- DualCool™ Package SON 5×6mm
- Optimized for Two Sided Cooling
- Optimized for 5V Gate Drive
- Ultralow Q<sub>q</sub> and Q<sub>qd</sub>
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant and Halogen Free

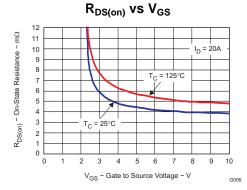
# **APPLICATIONS**

- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems
- Optimized for Synchronous or Control FET Applications

# **DESCRIPTION**

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.





#### PRODUCT SUMMARY

$V_{DS}$	Drain to Source Voltage	25		V
$Q_g$	Gate Charge Total (4.5V)	6.8		nC
$Q_{gd}$	Gate Charge Gate to Drain	1.3		nC
		$V_{GS} = 3V$	5.4	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 4.5V$	4.6	mΩ
		V <sub>GS</sub> = 8V 3.9		mΩ
V <sub>GS(th)</sub>	Threshold Voltage	1.1		V

#### ORDERING INFORMATION

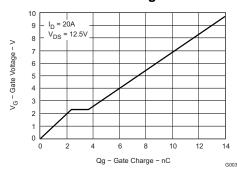
Device	Package	Media	Qty	Ship
CSD16322Q5C	SON 5x6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

### **ABSOLUTE MAXIMUM RATINGS**

T <sub>A</sub> = 25°C unless otherwise stated		VALUE	UNIT
$V_{DS}$	Drain to Source Voltage	25	٧
$V_{GS}$	Gate to Source Voltage	+10 / -8	<b>V</b>
	Continuous Drain Current, T <sub>C</sub> = 25°C	97	Α
I <sub>D</sub>	Continuous Drain Current <sup>(1)</sup>	21	Α
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	136	Α
$P_D$	Power Dissipation <sup>(1)</sup>	3.1	W
$T_J$ , $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to 150	°C
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D$ = 50A, L = 0.1mH, $R_G$ = 25 $\Omega$	125	mJ

- (1)  $R_{\theta JA} = 39$ °C/W on 1-inch<sup>2</sup> Cu, (2-oz.) on a 0.06" thick FR4 PCR
- (2) Pulse duration ≤300μs, duty cycle ≤2%

### **Gate Charge**



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## **ELECTRICAL CHARACTERISTICS**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Static C	haracteristics	·			
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_{DS} = 250 \mu A$	25		V
I <sub>DSS</sub>	Drain to Source Leakage	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 20V		1	μА
I <sub>GSS</sub>	Gate to Source Leakage	$V_{DS} = 0V, V_{GS} = +10/-8V$		100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9 1.1	1.4	V
		$V_{GS} = 3V$ , $I_{DS} = 20A$	5.4	7	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 4.5V$ , $I_{DS} = 20A$	4.6	5.8	mΩ
		V <sub>GS</sub> = 8V, I <sub>DS</sub> = 20A	3.9	5	mΩ
9 <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 15V, I <sub>DS</sub> = 20A	106		S
Dynamic	Characteristics	•			
C <sub>iss</sub>	Input Capacitance		1050	1365	pF
C <sub>oss</sub>	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V,$ $f = 1MHz$	740	950	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 10012	55	70	pF
R <sub>G</sub>	Series Gate Resistance		1.1	2.2	Ω
Qg	Gate Charge Total (4.5V)		6.8	9.7	nC
$Q_{gd}$	Gate Charge – Gate to Drain	$V_{DS} = 12.5V$ ,	1.3		nC
Q <sub>gs</sub>	Gate Charge – Gate to Source	I <sub>DS</sub> = 20A	2.4		nC
Q <sub>g(th)</sub>	Gate Charge at Vth		1.3		nC
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = 13V, V <sub>GS</sub> = 0V	17		nC
t <sub>d(on)</sub>	Turn On Delay Time		6.1		ns
t <sub>r</sub>	Rise Time	V <sub>DS</sub> = 12.5V, V <sub>GS</sub> = 4.5V,	10.7		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_{DS} = 20A$ , $R_G = 2\Omega$	12.3		ns
t <sub>f</sub>	Fall Time		3.7		ns
Diode C	haracteristics	•			
$V_{SD}$	Diode Forward Voltage	I <sub>DS</sub> = 20A, V <sub>GS</sub> = 0V	0.8	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	V 42V I 20A 4:/4t 20A / -	19		nC
t <sub>rr</sub>	Reverse Recovery Time	$V_{DD} = 13V$ , $I_F = 20A$ , $di/dt = 300A/\mu s$	21		ns

# THERMAL CHARACTERISTICS

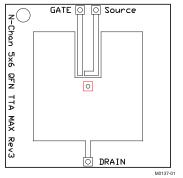
(T<sub>A</sub> = 25°C unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case (Top Source) <sup>(1)</sup>			3.5	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case (Bottom drain) <sup>(1)</sup>			2.4	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient <sup>(1)(2)</sup>			50	°C/W

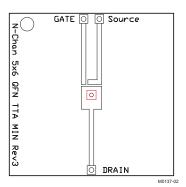
 $R_{\theta JC}$  is determined with the device mounted on a 1-inch<sup>2</sup> 2-oz. Cu pad on a 1.5 x 1.5-inch 0.06-inch thick FR4 board.  $R_{\theta JC}$  is specified by design, whereas  $R_{\theta CA}$  is determined by the user's board design. Device mounted on FR4 material with 1-inch² of 2-oz. Cu.

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Max  $R_{\theta JA} = 50$ °C/W when mounted on 1 inch<sup>2</sup> of 2-oz. Cu.



Max  $R_{\theta JA} = 123^{\circ}C/W$  when mounted on minimum pad area of 2-oz.Cu.

## TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

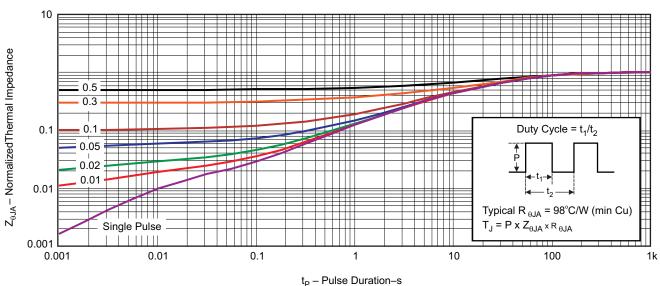


Figure 1. Transient Thermal Impedance

G012



# **TYPICAL MOSFET CHARACTERISTICS (continued)**

(T<sub>A</sub> = 25°C unless otherwise stated)

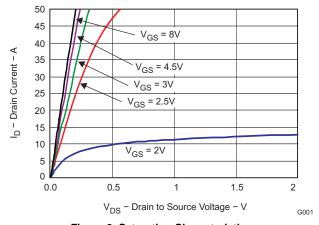


Figure 2. Saturation Characteristics

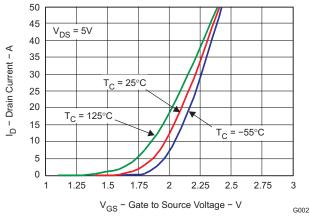


Figure 3. Transfer Characteristics

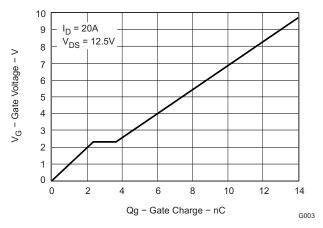


Figure 4. Gate Charge

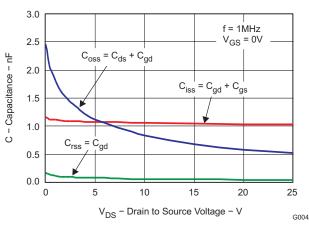


Figure 5. Capacitance

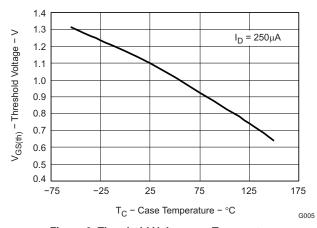


Figure 6. Threshold Voltage vs. Temperature

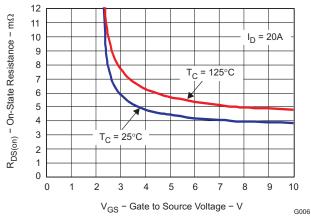


Figure 7. On Resistance vs. Gate Voltage



# **TYPICAL MOSFET CHARACTERISTICS (continued)**

(T<sub>A</sub> = 25°C unless otherwise stated)

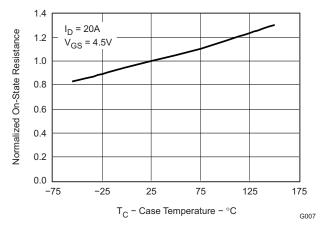


Figure 8. On Resistance vs. Temperature

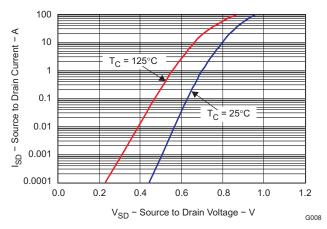


Figure 9. Typical Diode Forward Voltage

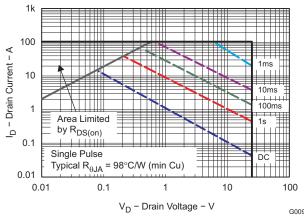


Figure 10. Maximum Safe Operating Area

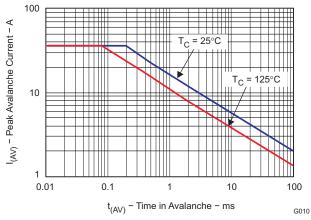


Figure 11. Single Pulse Unclamped Inductive Switching

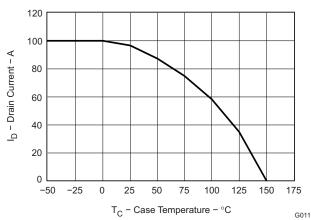
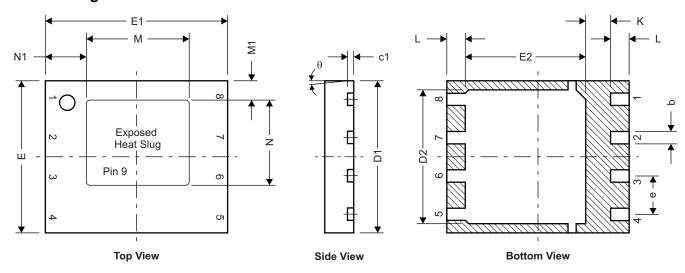


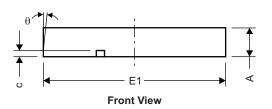
Figure 12. Maximum Drain Current vs. Temperature



# **MECHANICAL DATA**

# **Q5C Package Dimensions**





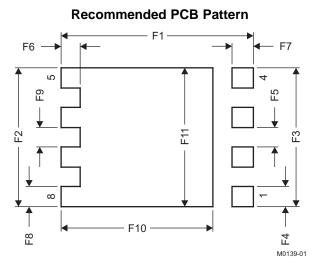
DualCool™Pinout			
Pin# Label			
1, 2, 3, 9 Source			
4	Gate		
5, 6, 7, 8 Drain			

M0162-01

DIM	MILLIM	ETERS	INC	HES
	MIN	MAX	MIN	MAX
Α	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
С	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
е	1.27	TYP	YP 0.050	
L	0.510	0.710	0.020	0.028
θ	-	-	-	-
K	0.760	-	0.030	_
М	3.260	3.460	0.128	0.136
M1	0.520	0.720	0.020	0.028
N	2.720	2.920	0.107	0.115
N1	1.227	1.427	0.048	0.056

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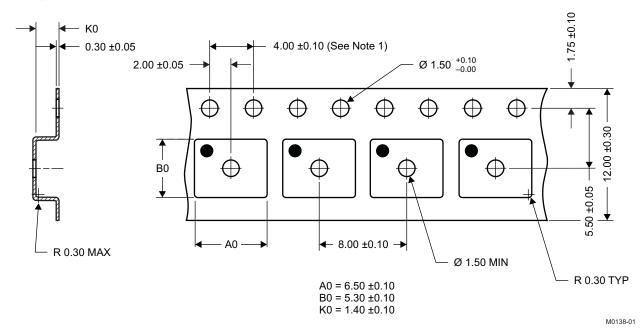




DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

# **Q5C Tape and Reel Information**



## Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and convection) PbF reflow compatible

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# **Package Marking Information**

Location
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### 1st Line

CSD = Fixed Characters

NNNNN = 5-digit Product Code

C = DualCool Package

#### 2nd Line (Date Code)

Y = Last digit of the Year

WW = 2-digit Work Week

C = Country of Origin

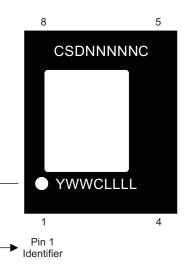
> Philippines = P

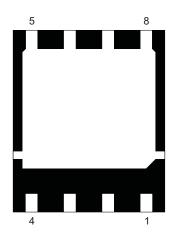
> Taiwan = T

> China = C

#### 3rd Line

LLLL = Last 4 digits of the Wafer Lot Number





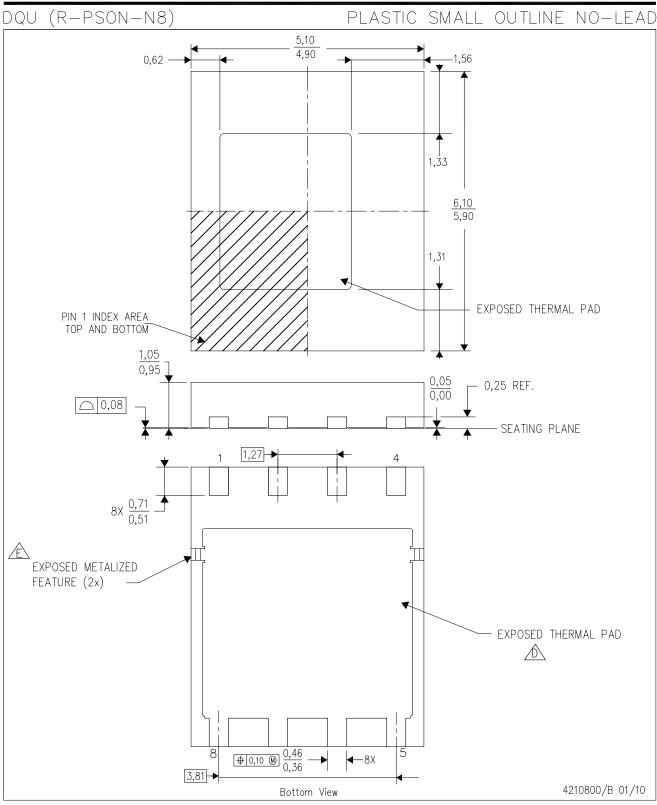
M0163-01

## **REVISION HISTORY**

### Changes from Original (December 2009) to Revision A

## **Page**

- Changed the Mechanical Data dimensions table. Added dimensions for M, M1, N and N1



- NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
  - B. This drawing is subject to change without notice.
  - C. Dual Cool No-Lead (SON) package configuration.
  - The package thermal pad must be soldered to the board for thermal and mechanical performance.
  - $ilde{\mathbb{A}}$  Metalized features are supplier options and may not be on the package.



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RFID	www.ti-rfid.com	Space, Avionics & Defense	www.ti.com/space-avionics-defense
RF/IF and ZigBee® Solutions	www.ti.com/lprf	Video and Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless-apps